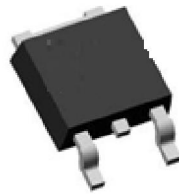


Main Product Characteristics

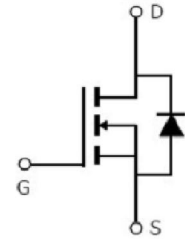
V_{DSS}	800V
$R_{DS(on)}$	3.8Ω (typ.)
I_D	3A



TO-252



Marking and Pin Assignment



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature
- Lead free product



Description

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating

Symbol	Parameter	Max.	Units
$I_D @ TC = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ①	3	A
$I_D @ TC = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ①	1.9	
I_{DM}	Pulsed Drain Current②	12	
$P_D @ TC = 25^\circ C$	Power Dissipation③	80	W
	Linear Derating Factor	0.64	W/°C
V_{DS}	Drain-Source Voltage	800	V
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy @ L=30mH	216	mJ
I_{AS}	Avalanche Current @ L=30mH	3.8	A
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C

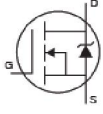
Thermal Resistance

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ^③	—	1.56	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-ambient ($t \leq 10s$) ^④	—	110	$^{\circ}C/W$
	Junction-to-Ambient (PCB mounted, steady-state) ^④	—	40	$^{\circ}C/W$

Electrical Characteristics@ $T_A=25^{\circ}C$ unless otherwise specified

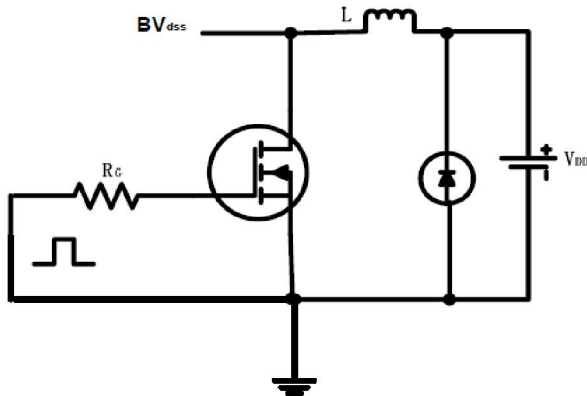
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	800	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	3.8	4.8	Ω	$V_{GS}=10V, I_D = 1.5A$ $T_J = 125^{\circ}C$
		—	8.9	—		
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$ $T_J = 125^{\circ}C$
		—	2.0	—		
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	$V_{DS} = 800V, V_{GS} = 0V$ $T_J = 125^{\circ}C$
		—	—	50		
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 30V$ $V_{GS} = -30V$
		—	—	-100		
Q_g	Total gate charge	—	11.2	—	nC	$I_D = 3A,$ $V_{DS}=400V,$ $V_{GS} = 10V$
Q_{gs}	Gate-to-Source charge	—	3.3	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	5.1	—		
$t_{d(on)}$	Turn-on delay time	—	11.3	—	ns	$V_{GS}=10V, V_{DS}=400V,$ $R_L=133\Omega,$ $R_{GEN}=25\Omega$ $I_D=3A$
t_r	Rise time	—	14.2	—		
$t_{d(off)}$	Turn-Off delay time	—	24.3	—		
t_f	Fall time	—	15.3	—		
C_{iss}	Input capacitance	—	386	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$
C_{oss}	Output capacitance	—	50.4	—		
C_{rss}	Reverse transfer capacitance	—	3.73	—		

Source-Drain Ratings and Characteristics

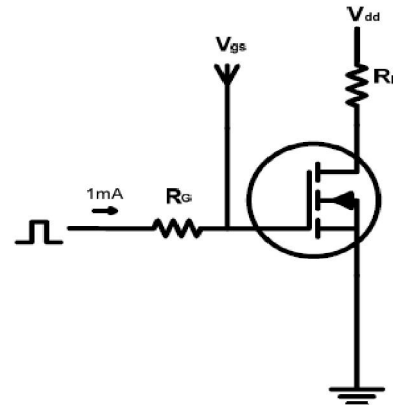
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	12	A	
V_{SD}	Diode Forward Voltage	—	0.88	1.4	V	$I_S=3A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	—	989	—	ns	$T_J = 25^{\circ}C, I_F = 3A,$ $di/dt = 100A/\mu s$
Q_{rr}	Reverse Recovery Charge	—	2405	—	nC	

Test Circuits and Waveforms

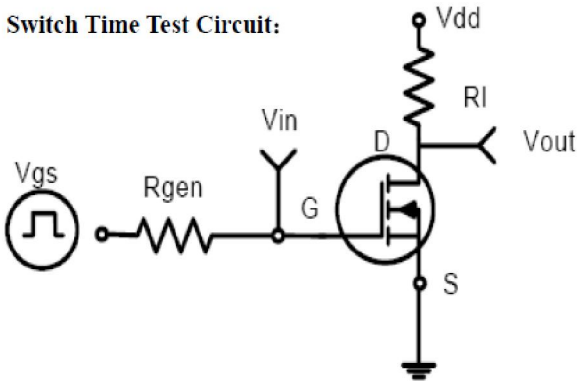
EAS test circuits:



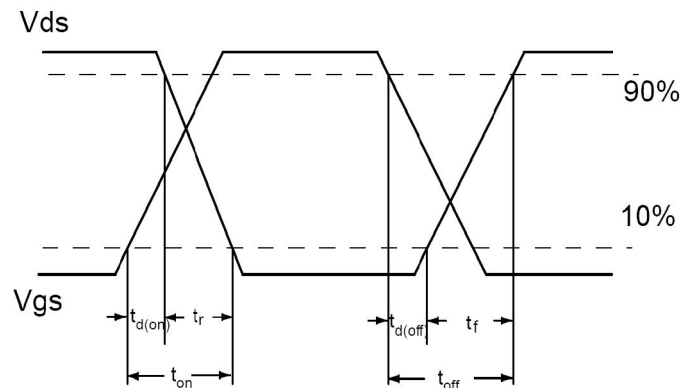
Gate charge test circuit:



Switch Time Test Circuit:



Waveforms:



Notes:

- ① The maximum current rating is limited by bond-wires.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$

Typical Electrical and Thermal Characteristics

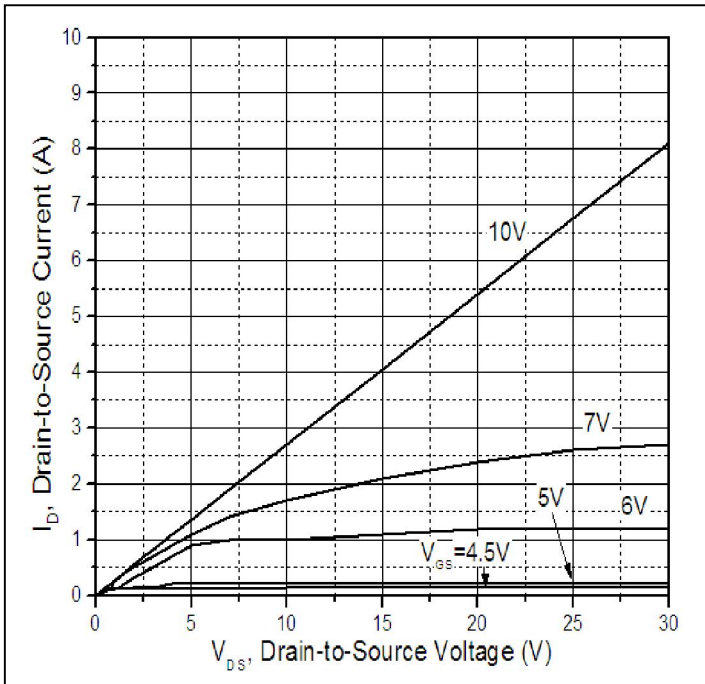


Figure 1: Typical Output Characteristics

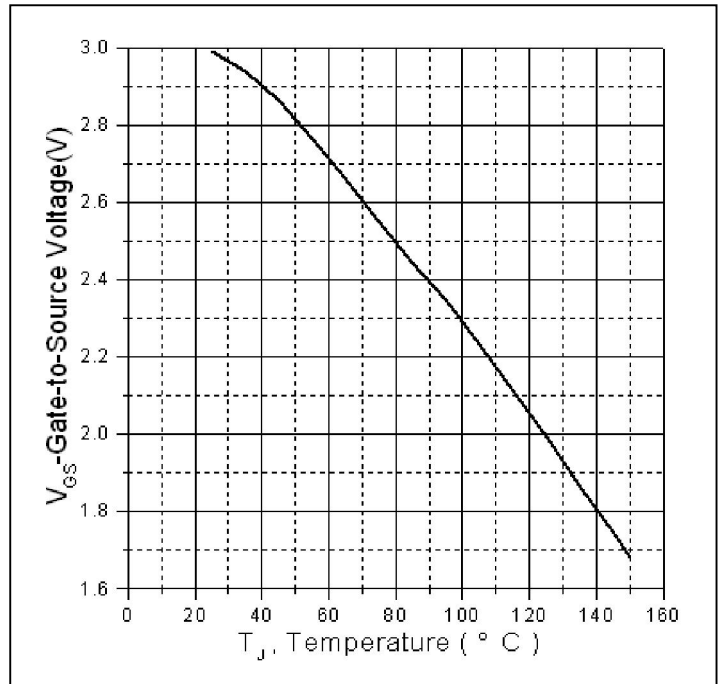


Figure 2. Gate to source cut-off voltage

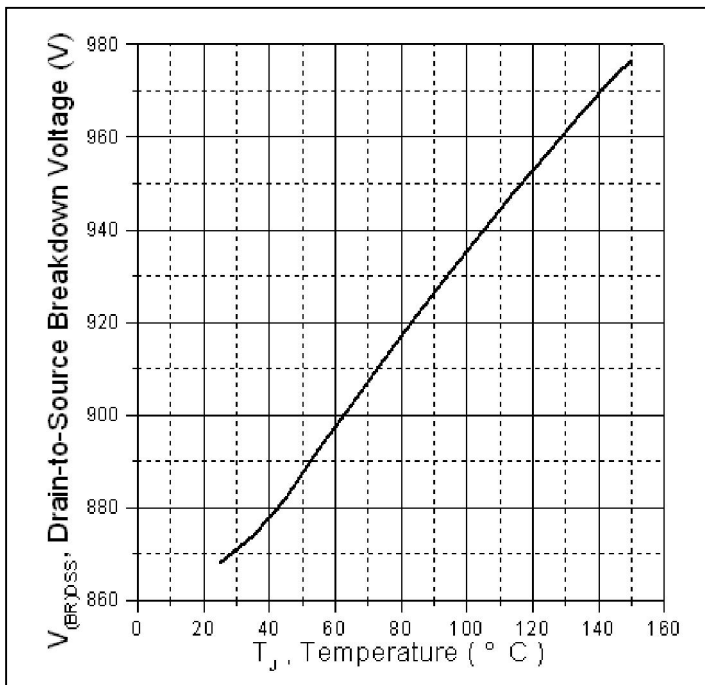


Figure 3. Drain-to-Source Breakdown Voltage Vs. Case Temperature

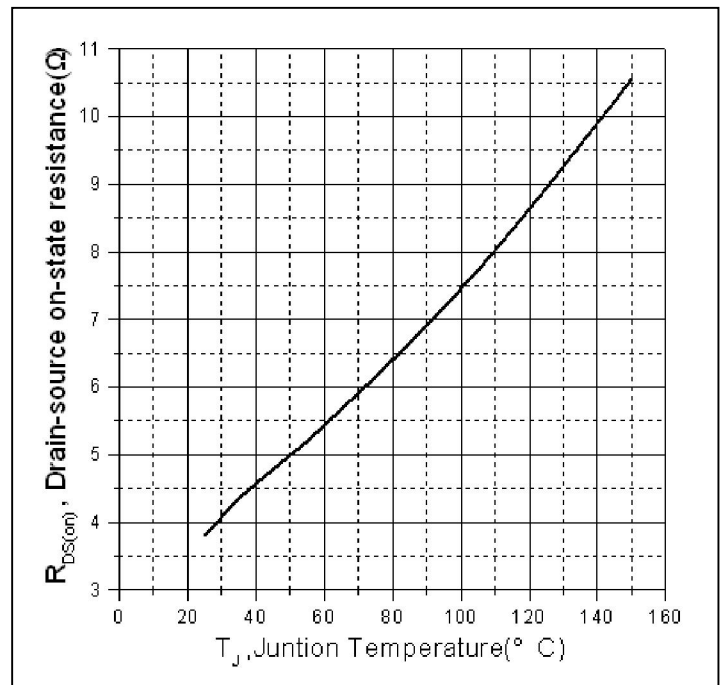


Figure 4: Normalized On-Resistance Vs. Case Temperature

Typical Electrical and Thermal Characteristics

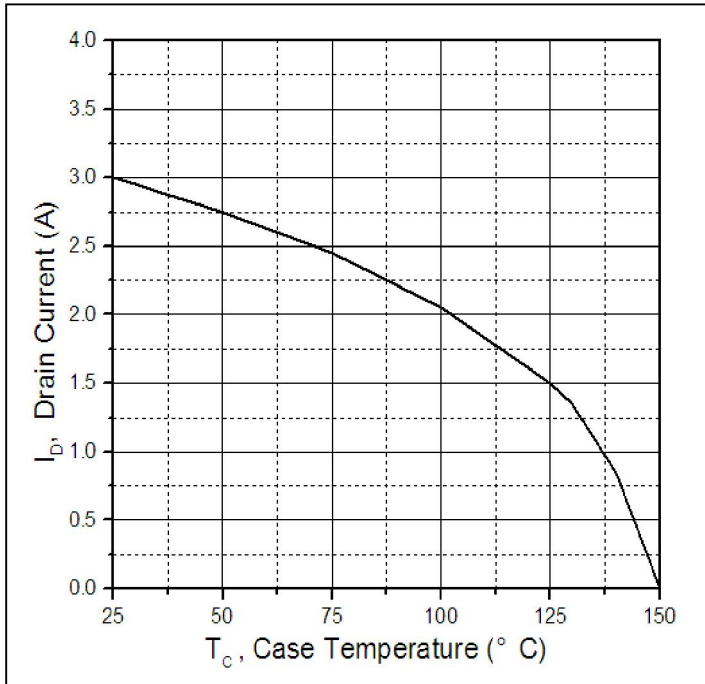


Figure 5. Maximum Drain Current Vs. Case Temperature

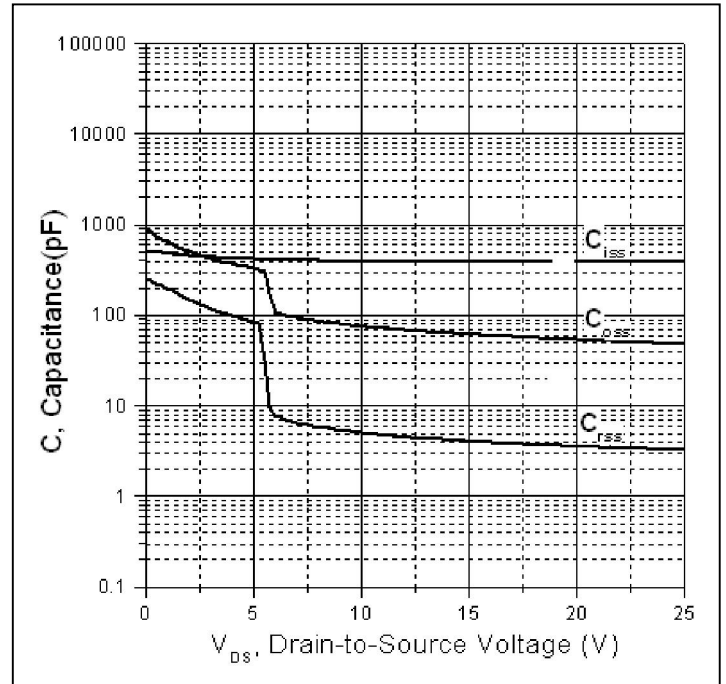
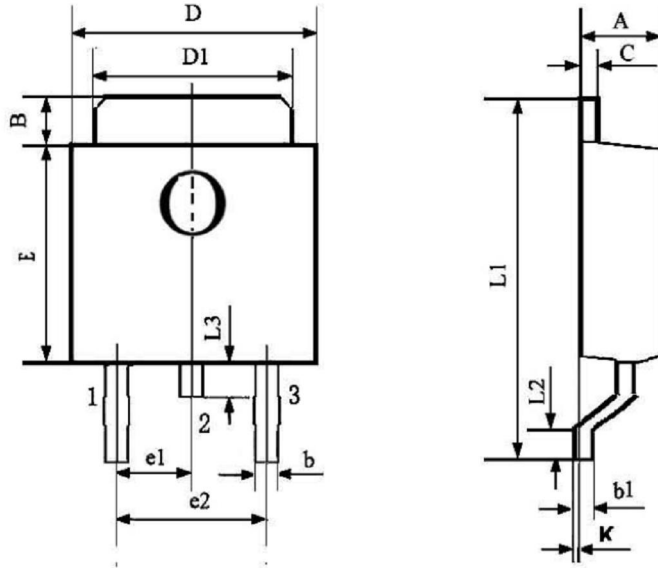


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

Mechanical Data

TO-252 PACKAGE OUTLINE DIMENSION



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	2.200	-	2.400	0.087	-	0.094
B	0.950	-	1.250	0.037	-	0.049
b	0.500	-	0.700	0.020	-	0.028
b1	0.450	-	0.550	0.018	-	0.022
C	0.450	-	0.550	0.018	-	0.022
D	6.450	-	6.750	0.254	-	0.266
D1	5.200	-	5.400	0.205	-	0.213
E	5.950	-	6.250	0.234	-	0.246
e1	2.240	-	2.340	0.088	-	0.092
e2	4.430	-	4.730	0.174	-	0.186
L1	9.450	-	9.950	0.372	-	0.392
L2	1.250	-	1.750	0.049	-	0.069
L3	0.600	-	0.900	0.024	-	0.035
K	0.000	-	0.100	0.000	-	0.004



Ordering and Marking Information

Device Marking: SSF3N80D

Package (Available)
TO-252 (DPAK)
Operating Temperature Range
C : -55 to 150 °C

Devices per Unit (options)

Package Type	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO-252	2500	2	5000	7	35000
TO-252	2500	1	2500	10	25000
TO-252	800	5	4000	8	32000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	$T_j=125^{\circ}\text{C}$ to 150°C @ 80% of Max $V_{DSS}/V_{CES}/V_R$	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	$T_j=150^{\circ}\text{C}$ @ 100% of Max V_{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices